

In the Specification:

Page 9, paragraph 1:

Figure 3 shows a substrate 302 covered by a layer of insulating material 304, preferably oxide. A trench 306 is etched in the oxide, followed by formation of sidewalls 308 in the trench. A conducting material 310 (preferably polysilicon) is deposited in the trench. (Note that in some embodiments, an electrical interconnect is also present, connecting the trench fill material to another voltage element.) The surface is then planarized and covered by another insulating layer of oxide 312, followed by formation of the active area 314 and the gate 316.

Page 9, paragraph 4:

Figure 4 shows a substrate material 402 with an insulating layer 404 and the conducting trench filler 406. And The a transistor comprises the a body of active material 408 covers the trench fill 406[. A], a gate structure 410 is shown over the active body 408[. Gate], and a gate oxide 414 is also shown.